

Description

The AR3311D3L is a 3.3V bi-directional TVS diode, utilizing leading monolithic silicon technology to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive high-speed data lines. The AR3311D3L has a low capacitance with a typical value at 1pF, and complies with the IEC 61000-4-2 (ESD) with ±30kV air and ±30kV contact discharge. It is assembled into a lead-free SOD-323 package. The small size, low capacitance and high ESD surge protection make AR3311D3L an ideal choice to protect cell phone, wireless systems, and communication equipment.

Features

180W peak pulse power (8/20µs)

Ultra low capacitance: 1pF typical

Ultra low leakage: nA level

Operating voltage: 3.3V

Low clamping voltage

Protects one power line or data line

Complies with following standards:

IEC 61000-4-2 (ESD) immunity test
 Air discharge: ±30kV

Contact discharge: ±30kV – IEC61000-4-5 (Lightning) 12A (8/20µs)

RoHS Compliant

Mechanical Characteristics

Package: SOD-323Lead Finish: Matte Tin

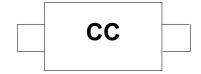
Case Material: "Green" Molding Compound.Terminal Connections: See Diagram Below

Marking Information: See Below

Applications

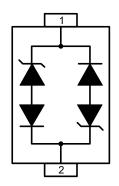
- USB Ports
- Smart Phones
- Wireless Systems
- Ethernet 10/100/1000 Base T

Marking Information



Ordering Information

Dimensions and Pin Configuration



Circuit and Pin Schematic

Part Number	Packaging	Reel Size
AR3311D3L	3000/Tape & Reel	7 inch



Absolute Maximum Ratings (T_A=25°C unless otherwise specified)

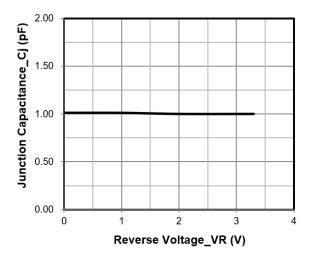
Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20µs)	Ppk	180	W
Peak Pulse Current (8/20µs)	IPP	12	Α
ESD per IEC 61000-4-2 (Air)	VESD	±30	kV
ESD per IEC 61000-4-2 (Contact)	VESD	±30	۸V
Operating Temperature Range	TJ	-55 to +125	°C
Storage Temperature Range	Tstg	-55 to +150	°C

Electrical Characteristics (T_A=25°C unless otherwise specified)

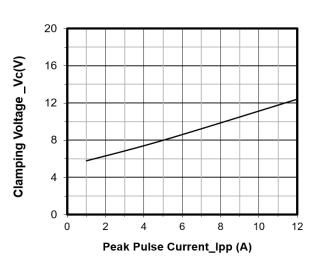
Parameter	Symbol	Min	Тур	Max	Unit	Test Condition
Reverse Working Voltage	VRWM			3.3	V	
Breakdown Voltage	VBR	3.8			V	IT = 1mA
Reverse Leakage Current	I _R			0.2	μA	VT=VRWM
Clamping Voltage	Vc			7	V	IPP = 1A (8 x 20μs pulse)
Clamping Voltage	Vc			15	V	IPP = 12A (8 x 20µs pulse)
Junction Capacitance	CJ		1		pF	VR = 0V, f = 1MHz



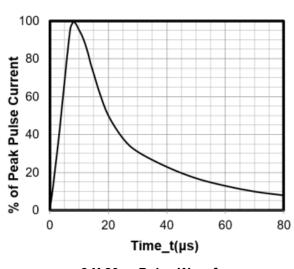
Typical Performance Characteristics (TA=25°C unless otherwise Specified)



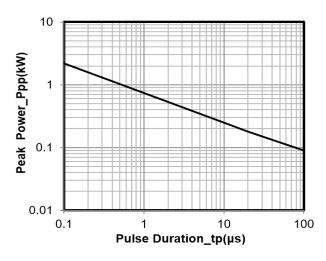
Junction Capacitance vs. Reverse Voltage



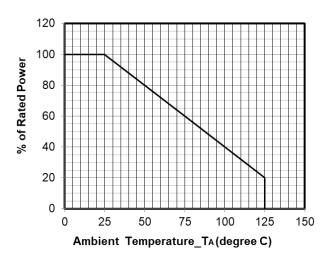
Clamping Voltage vs. Peak Pulse Current



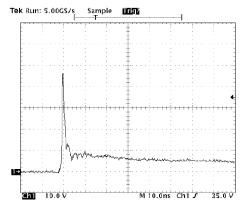
8 X 20µs Pulse Waveform



Peak Pulse Power vs. Pulse Time



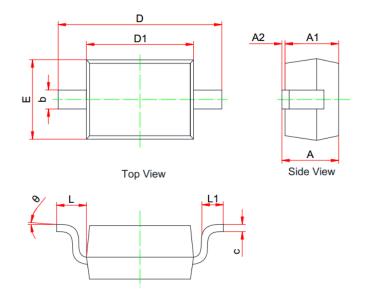
Power Derating Curve



Note: Data is taken with a 10x attenuator
ESD Clamping Voltage
8 kV Contact per IEC61000-4-2



SOD-323 Package Outline Drawing



	MILLIMETERS				
	MIN	NOM	MAX		
Α	0.800		1.100		
A1	0.800		0.900		
A2	0.000		0.100		
b	0.250		0.400		
С	0.080		0.177		
D1	1.600	1.700	1.800		
D	2.300		2.800		
E	1.150		1.400		
L	0.475REF				
L1	0.100		0.500		
Θ	0°		8°		

Suggested Land Pattern



Unit: mm

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